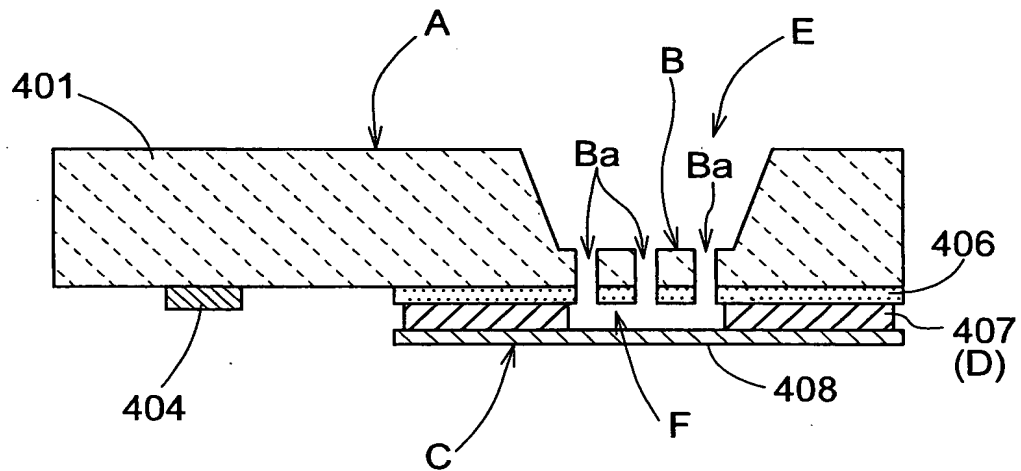


FIG.1



A: substrate  
 B: back electrode  
 Ba: perforations  
     (acoustic holes)  
 C: diaphragm  
 D: spacer  
 E: acoustic opening  
 F: void area

401: silicon substrate  
 404: electrode portion  
 406: second protective film  
 407: sacrificial layer  
 408: metal film

FIG.2

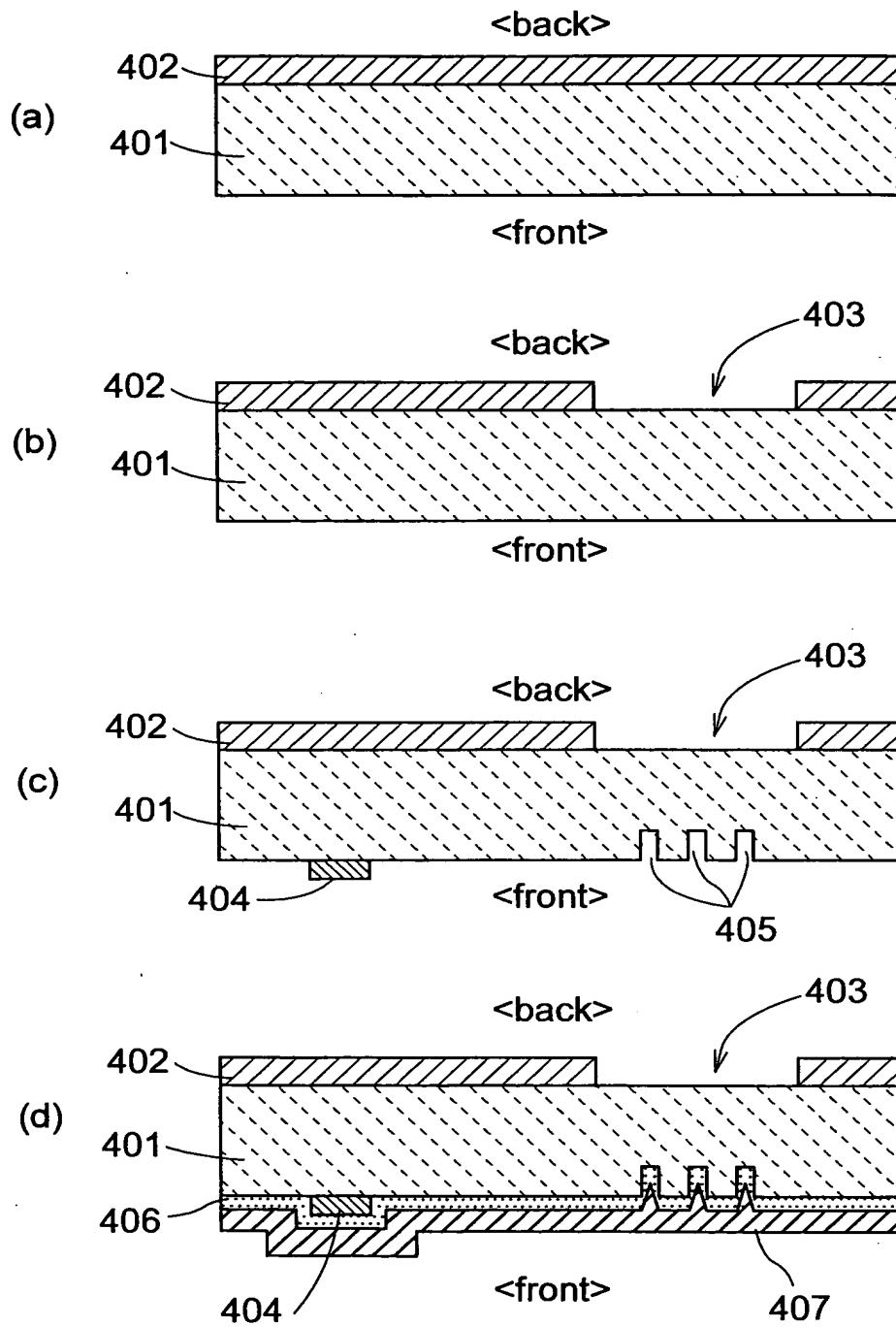


FIG.3

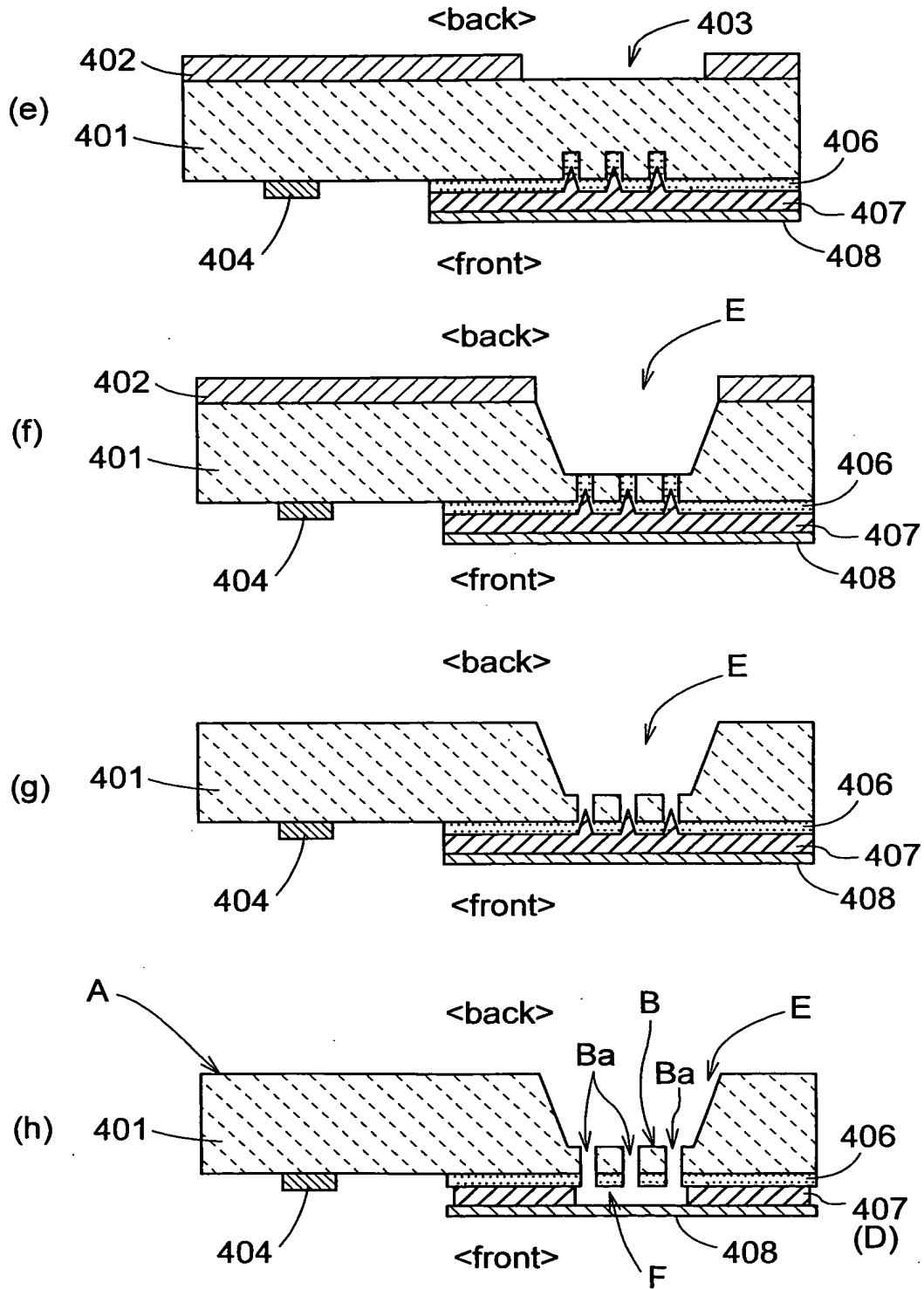


FIG.4

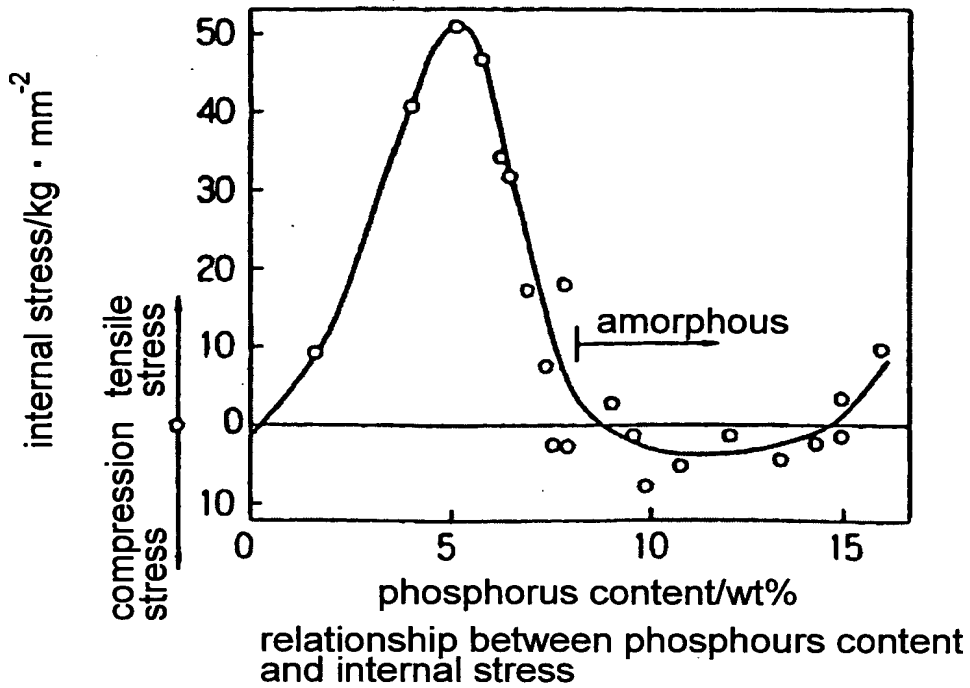
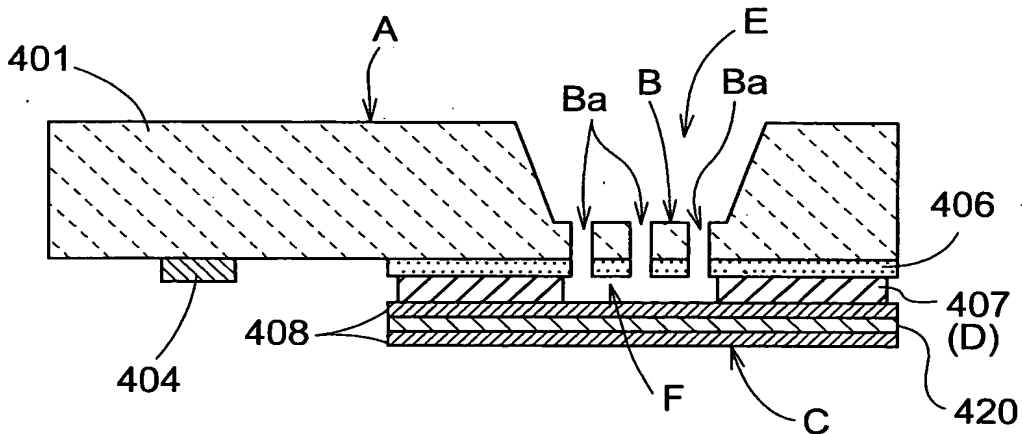


FIG.5



A: substrate

B: back electrode

Ba: perforations  
(acoustic holes)

C: diaphragm

D: spacer

E: acoustic opening

F: void area

401: silicon substrate

404: electrode portion

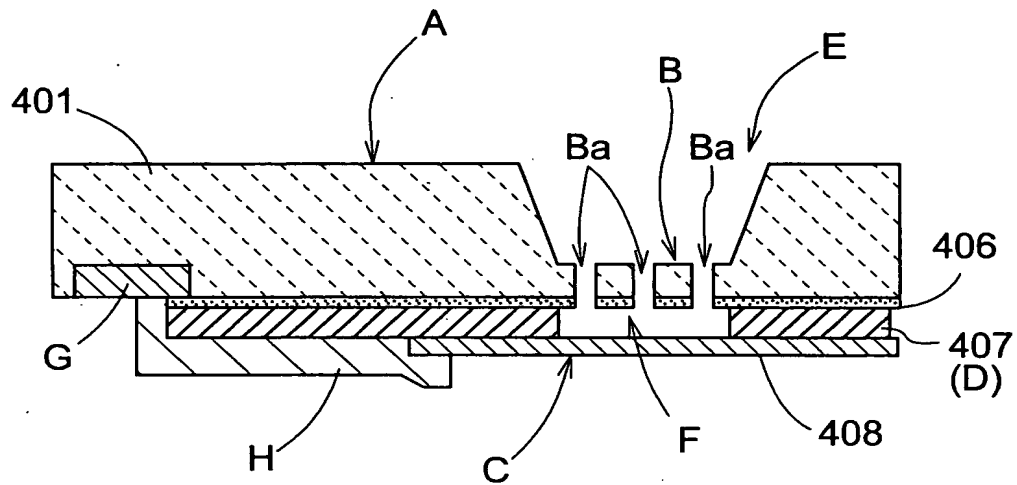
406: second protective film

407: sacrificial layer

408: metal film

420: base layer

FIG.6



A: substrate  
 B: back electrode  
 Ba: perforations  
     (acoustic holes)  
 C: diaphragm  
 D: spacer  
 E: acoustic opening  
 F: void area  
 G: integrated circuit  
 H: wiring

401: silicon substrate  
 406: second protective film  
 407: sacrificial layer  
 408: metal film

FIG. 7

PRIOR ART

